

N-channel 100V 13.9mΩ standard level MOSFET in TO220. 10 August 2012 Product data sheet

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### **1.2 Features and benefits**

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

### 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	68	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics		I				
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 12		-	19.4	25	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 13	[2]	-	10.8	13.9	mΩ
Dynamic ch	naracteristics	1	ı	1	1		
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; Fig. 15; Fig. 14		-	17	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 14; Fig. 15</u>		-	59	-	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})} \texttt{=} 25 \; ^{\circ}\text{C}; \; I_{D} \texttt{=} 68 \; A; \\ V_{sup} \texttt{\leq} 100 \; V; \; \text{unclamped}; \; R_{GS} \texttt{=} 50 \; \Omega \end{array}$		-	-	128	mJ

Continuous current is limited by package Measured 3 mm from package. [1]

[2]

#### 2. **Pinning information**

D	0	Description of the second s		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G - U - T - T - T - T - T - T - T - T - T
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

#### **Ordering information** 3.

Table 3. Ordering int	formation					
Type number	Package	Package				
	Name	Description	Version			
PSMN013-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

#### Marking 4.

Table 4. Marking codes	
Type number	Marking code
PSMN013-100PS	PSMN013-100PS

#### N-channel 100V 13.9m $\Omega$ standard level MOSFET in TO220.

### 5. Limiting values

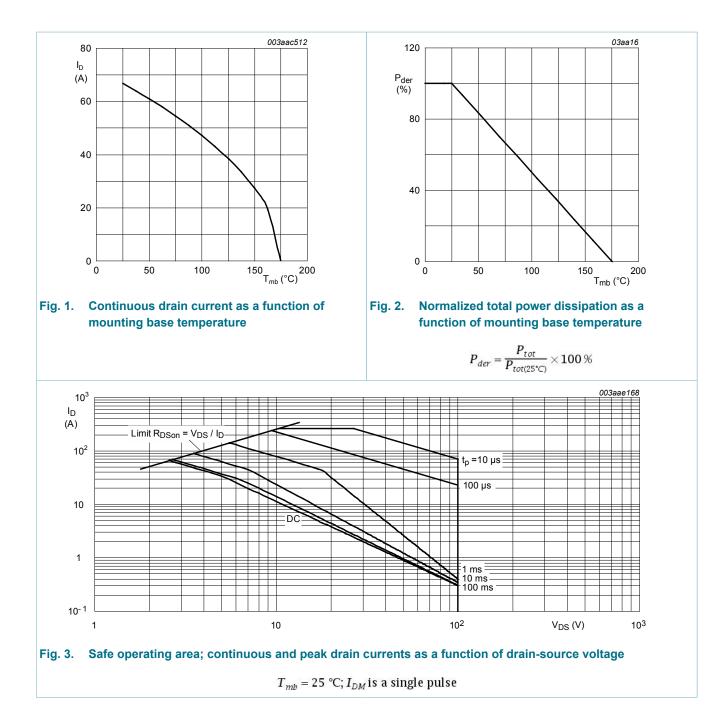
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	47	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	68	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	272	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	170	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	68	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	272	Α
Avalanche	ruggedness	·				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 68 A; V <sub>sup</sub> ≤ 100 V; unclamped; R <sub>GS</sub> = 50 Ω		-	128	mJ

[1] Continuous current is limited by package

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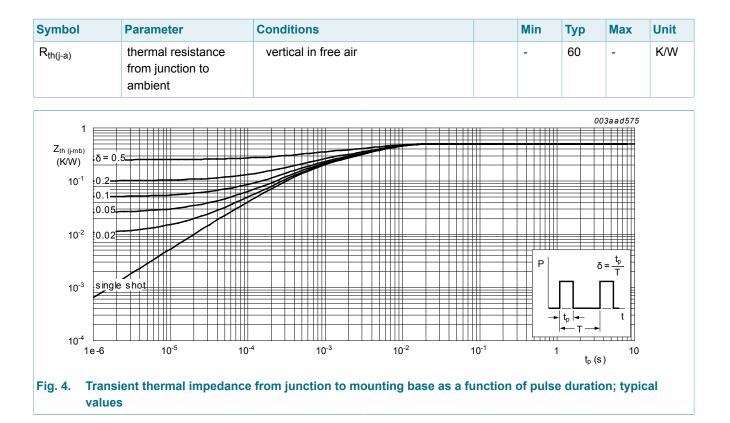
### 6. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.5	0.9	K/W

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### 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	100	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.06	2	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 12	-	19.4	25	mΩ

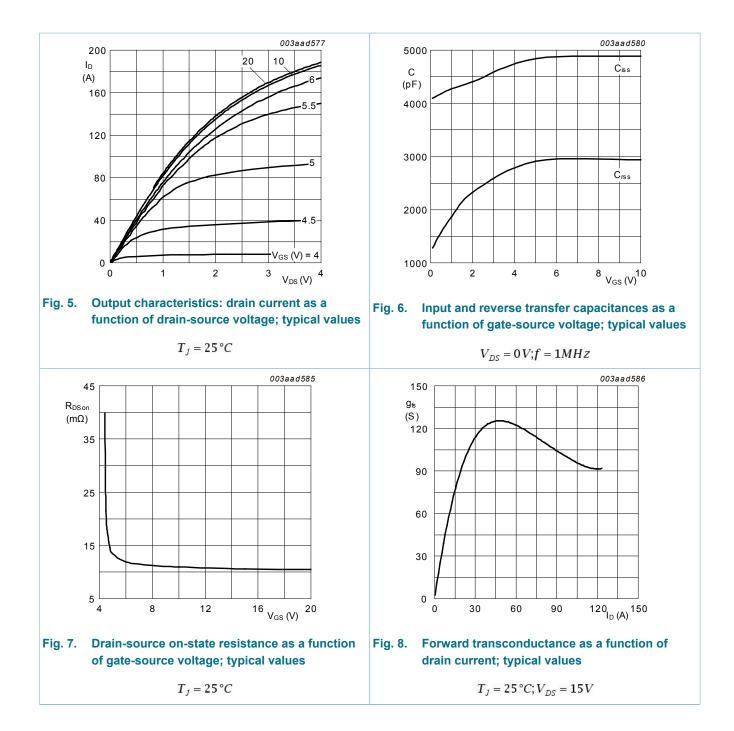
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; <u>Fig. 12</u>		-	29.5	38.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	[1]	-	10.8	13.9	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic ch	naracteristics						
Q <sub>G(tot)</sub> total gate charge		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	59	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V		-	47.6	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	13.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 15		-	9.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate- source charge			-	4.6	-	nC
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 15; Fig. 14		-	17	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 50 V; <u>Fig. 15; Fig. 14</u>		-	4.4	-	V
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz;		-	3195	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	221	-	pF
C <sub>rss</sub>	reverse transfer capacitance	-		-	136	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; $R_L$ = 2 $\Omega$ ; $V_{GS}$ = 10 V;		-	20.7	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 4.7 Ω; T <sub>j</sub> = 25 °C		-	25	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	52.5	-	ns
t <sub>f</sub>	fall time			-	24	-	ns
Source-dra	in diode	1	1				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 25 A; dI <sub>S</sub> /dt = 100 A/µs; V <sub>GS</sub> = 0 V;		-	52	-	ns
Qr	recovered charge	V <sub>DS</sub> = 50 V		-	109	-	nC

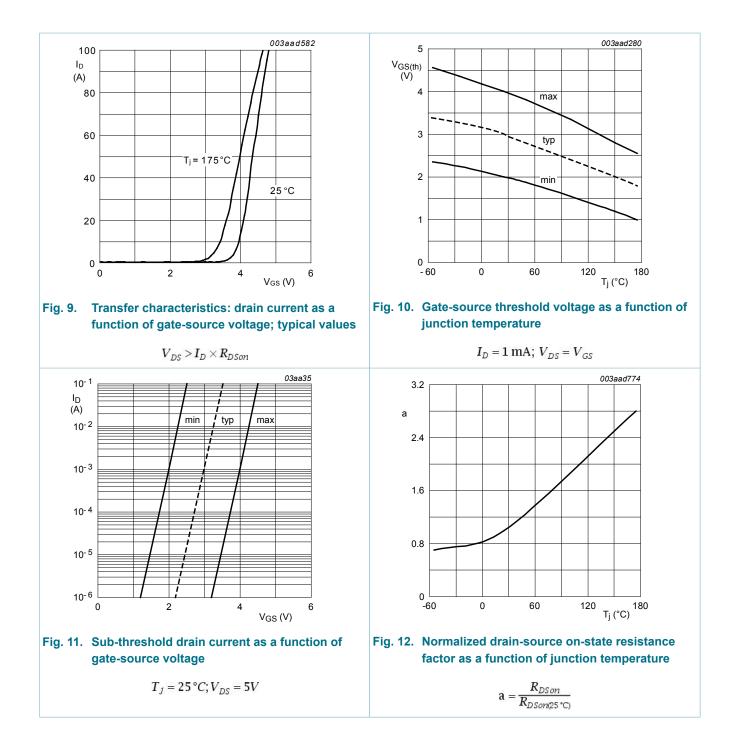
[1] Measured 3 mm from package.

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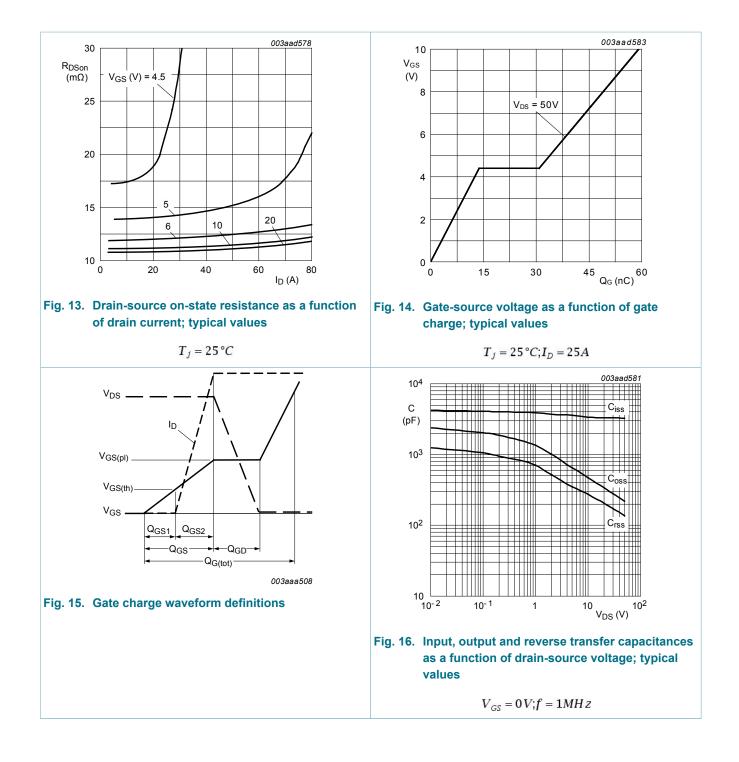


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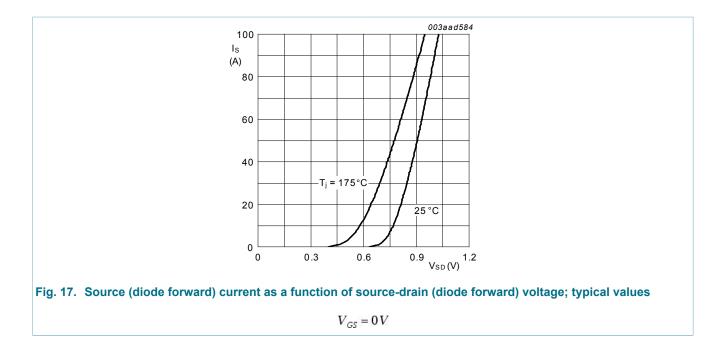
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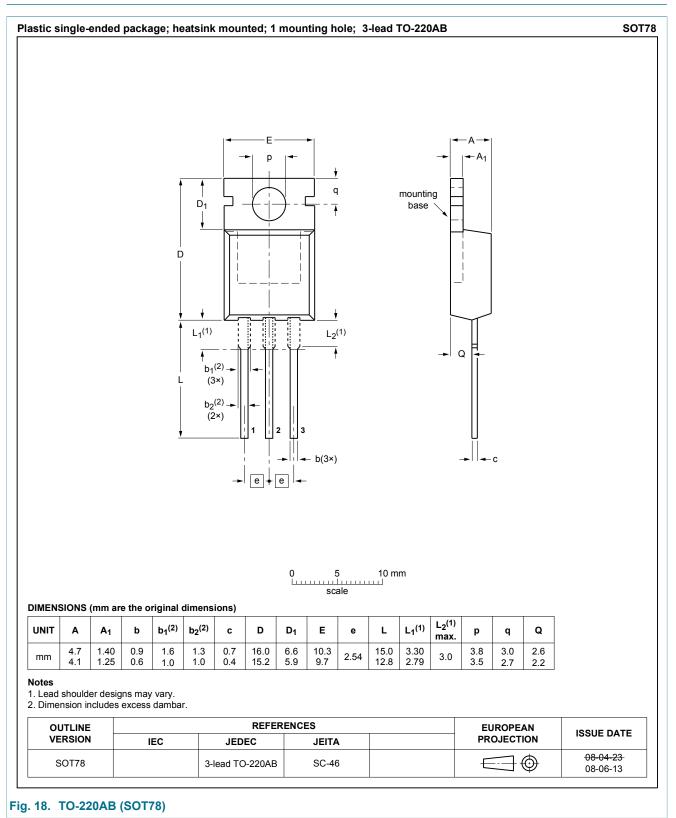
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### N-channel 100V 13.9m $\Omega$ standard level MOSFET in TO220.



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### 8. Package outline



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#### N-channel 100V 13.9mΩ standard level MOSFET in TO220.

### 9. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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